

United States Patent and Trademark Office

UNITED STATES DEPARTMENT OF COMMERCE United States Patent and Trademark Office Address: COMMISSIONER FOR PATENTS P.O. Box 1450 Alexandria, Virginia 22313-1450 www.uspto.gov

APPLICATION NO.	FII	LING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO
10/646,608	08/21/2003		Charles E. Larson	108298502US2	9809
25096	7590	06/11/2004		EXAMINER	
PERKINS (COIE LLE		TOLEDO, FERNANDO L		
PATENT-SE P.O. BOX 12				ART UNIT	PAPER NUMBER
SEATTLE, WA 98111-1247				2823	

DATE MAILED: 06/11/2004

Please find below and/or attached an Office communication concerning this application or proceeding.

	Application No.	Applicant(s)					
	10/646,608	LARSON ET AL.					
Office Action Summary	Examin r	Art Unit					
	Fernando L. Toledo	2823					
The MAILING DATE of this communicati n appears on the c ver sheet with the correspondence address Period for Reply							
A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION. - Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely. - If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication. - Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).							
Status							
 Responsive to communication(s) filed on <u>21 At</u> This action is FINAL. 2b) This Since this application is in condition for allowar closed in accordance with the practice under E 	action is non-final. nce except for formal matters, pro						
Disposition of Claims							
4) ☐ Claim(s) 69-81 is/are pending in the application 4a) Of the above claim(s) is/are withdray 5) ☐ Claim(s) is/are allowed. 6) ☐ Claim(s) 69-81 is/are rejected. 7) ☐ Claim(s) is/are objected to. 8) ☐ Claim(s) are subject to restriction and/or	vn from consideration.						
Application Papers							
9) ☐ The specification is objected to by the Examine 10) ☑ The drawing(s) filed on 21 August 2003 is/are: Applicant may not request that any objection to the Replacement drawing sheet(s) including the correct 11) ☐ The oath or declaration is objected to by the Ex	a) \boxtimes accepted or b) \square objected the drawing (s) be held in abeyance. See ion is required if the drawing (s) is object.	e 37 CFR 1.85(a). jected to. See 37 CFR 1.121(d).					
Priority under 35 U.S.C. § 119							
 12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f). a) All b) Some * c) None of: 1. Certified copies of the priority documents have been received. 2. Certified copies of the priority documents have been received in Application No. 3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)). * See the attached detailed Office action for a list of the certified copies not received. 							
Attachment(s) 1) Notice of References Cited (PTO-892) 2) Notice of Draftsperson's Patent Drawing Review (PTO-948) 3) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08) Paper No(s)/Mail Date 20030821.	4) Interview Summary Paper No(s)/Mail Da 5) Notice of Informal P 6) Other:						

DETAILED ACTION

Claim Rejections - 35 USC § 103

- 1. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
 - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 2. Claims 69 76 and 78 81 are rejected under 35 U.S.C. 103(a) as being unpatentable over Bayraktaroglu (U. S. patent 5,496,755) in view of Bruel (U. S. patent 5,374,564).

In re claim 69, Bayraktaroglu in the U. S. patent 5,496,755; figures 1 – 4 and related text discloses a substrate having a first portion with a first surface, the first portion having first and second voids extending from the first surface to a separation plane, the first void tapered along a first axis and the second void tapered along a second axis generally parallel to the first axis, the first and second tapered voids being larger toward the separation line; and at least one operable microelectronic device disposed at least proximate to the first surface and between the first and second axes (Figure 4).

Bayraktaroglu does not show a second portion with a second surface opposite the first surface and a separation plane between the first and second portions.

However, Bruel in the U. S. patent 5,374,564; figures 1-4 and related text discloses an alternative method to form thin substrates without requiring an initial substrate of a different nature from that of the chosen semiconductor, without requiring very high implantation dosage,

or an etch-stop, but which still makes possible to obtain a uniform, controlled thickness (Column 2, lines 5-13).

It would have been obvious to one having ordinary skill in the art at the time the invention was made to form the substrate of Bayraktaroglu by having a larger substrate and then cutting through a predetermined separation line as taught by Bruel, since, it can be done without requiring an initial substrate of a different nature from that of the chosen semiconductor, without requiring very high implantation dosage, or an etch-stop, but which still makes possible to obtain a uniform, controlled thickness.

- 3. In re claim 70, Bayraktaroglu discloses wherein the microelectronic device is disposed in the first portion of the substrate between the first and second tapered voids (Figure 4).
- 4. In re claim 71, Bayraktaroglu in view of Bruel discloses wherein the first portion and the second portion have at least generally the same composition. (Column 2 of Bruel).
- 5. In re claim 72, Bayraktaroglu teaches wherein the first external surface is separated from the second external surface by about 150 microns or less (column 5).
- 6. In re claim 73, Bayraktaroglu teaches wherein the voids are etched voids (column 5).
- 7. In re claim 74, Bayraktaroglu teaches wherein the first portion further includes a third void extending from the first surface to the separation plane, and wherein the first, second and third voids are regularly spaced apart from each other (figure 4 and claim 4).
- 8. In re claim 75, Bayraktaroglu discloses wherein the first portion further includes a third void extending from the first surface to the separation plane, and wherein the first, second and third voids are randomly spaced apart from each other (figure 4 and claim 4).

9. In re claim 76, Bayraktaroglu discloses wherein the first and second voids each include a first end proximate to the first surface, and wherein the first ends are filled with a filler material (figure 4).

- 10. In re claim 78, Bayraktaroglu discloses further including a film layer disposed on the first surface (figure 4).
- 11. In re claim 79, Bayraktaroglu discloses wherein the film layer has an external surface facing an opposite direction form the second surface of the second portion, and wherein a distance between the external surface and the separation plane is less than approximately 150 microns (column 3).
- 12. In re claim 80, Bayraktaroglu discloses wherein the first and second voids have a conical configuration (figure 4).
- 13. In re claim 81, Bayraktaroglu discloses wherein the first void has a first depth and the second void has a second depth at least approximately equal to the first depth (figure 4).
- 14. Claim 77 is rejected under 35 U.S.C. 103(a) as being unpatentable over Bayraktaroglu in view of Bruel as applied to claims 69 76 and 78 81 above, and further in view of Wolf and Tauber (Silicon Processing for the VLSI Era Volume 1: Process Technology).

Bayraktaroglu in view of Bruel does not disclose wherein the semiconductor substrate is made of silicon.

However, Wolf, in the textbook, Silicon Processing for the VLSI Era Volume 1: Process Technology, page 1, discloses that silicon is the most important semiconductor material for the electronics industry among its advantages is that is readily available and therefore cheap compared to other semiconductor materials (page 1).

Application/Control Number: 10/646,608

Art Unit: 2823

It would have been obvious to one having ordinary skill in the art at the time the.

Page 5

invention was made to use silicon to form the substrate of Bayraktaroglu since, as taught by

Wolf, silicon is the most important semiconductor material for the electronics industry among its

advantages is that is readily available and therefore cheap compared to other semiconductor

materials.

Conclusion

Any inquiry concerning this communication or earlier communications from the

examiner should be directed to Fernando L. Toledo whose telephone number is 571-272-1867.

The examiner can normally be reached on Mon-Thu 7am to 5:30pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's

supervisor, Olik Chaudhuri can be reached on 571-272-1855. The fax phone number for the

organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent

Application Information Retrieval (PAIR) system. Status information for published applications

may be obtained from either Private PAIR or Public PAIR. Status information for unpublished

applications is available through Private PAIR only. For more information about the PAIR

system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR

system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Olik Chaudhuri

Supervisory Primary Examiner

Art Unit 2823

Maledo